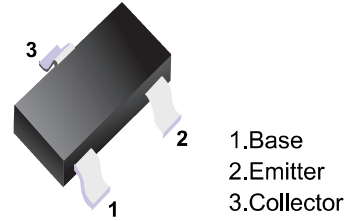


■ NPN Transistors
■ Features

- High Collector Current
- Complementary to SS8550W

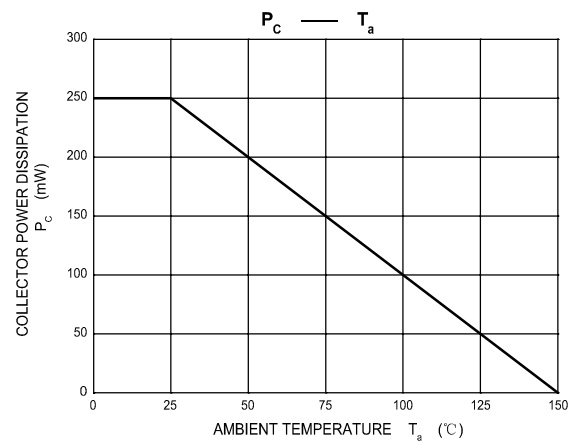
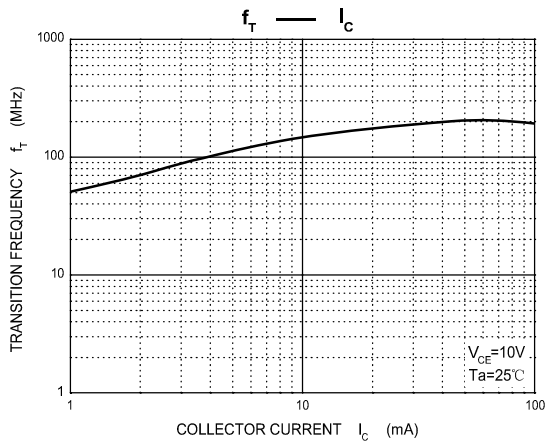
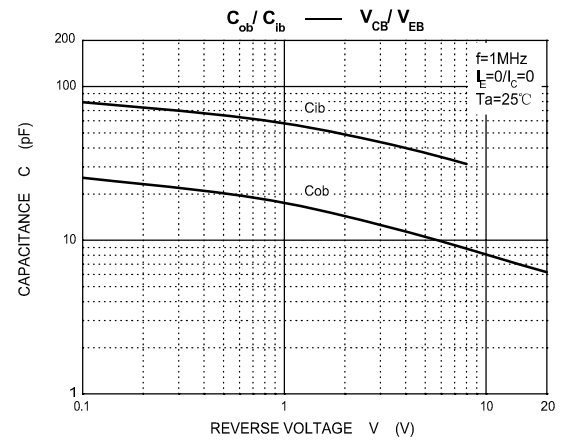
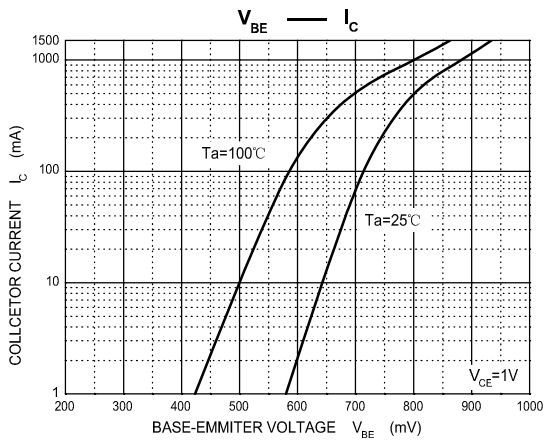
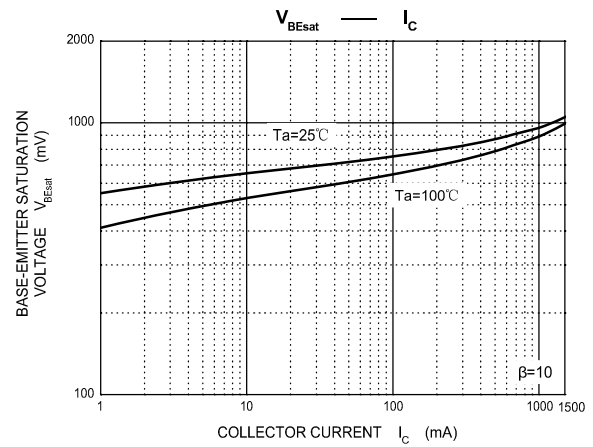
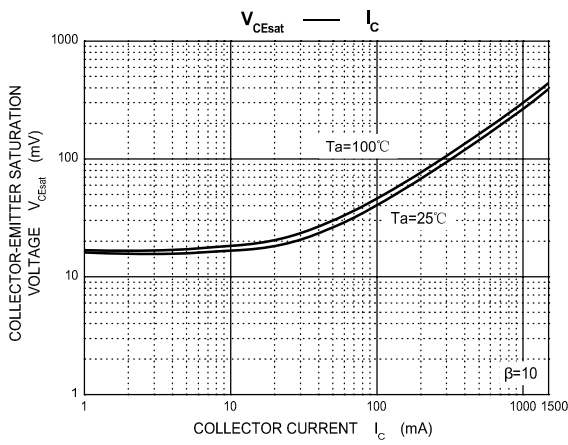
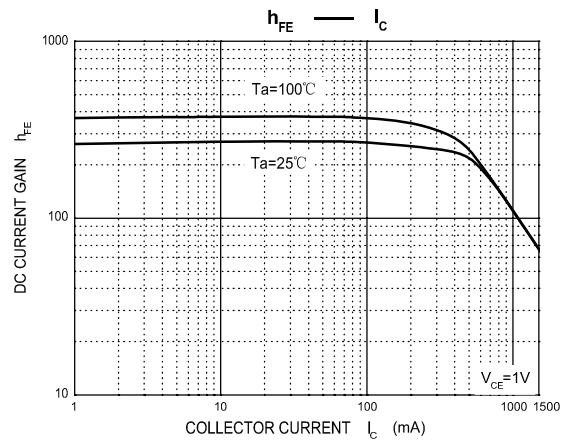
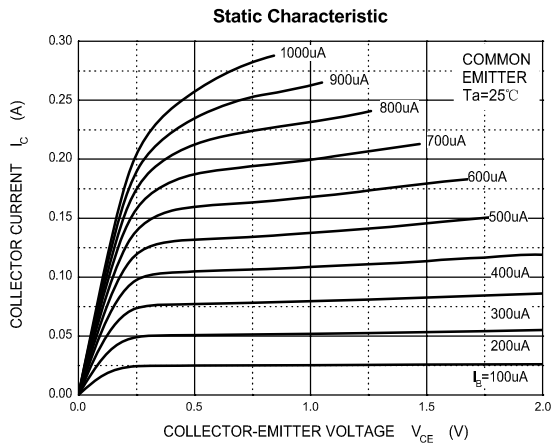

■ Simplified outline(SOT-323)
■ Absolute Maximum Ratings Ta = 25°C

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EB0}	Emitter-Base Voltage	5	V
I _C	Collector Current	1.5	A
P _C	Collector Power Dissipation	250	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	500	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

■ Electrical Characteristics Ta = 25°C

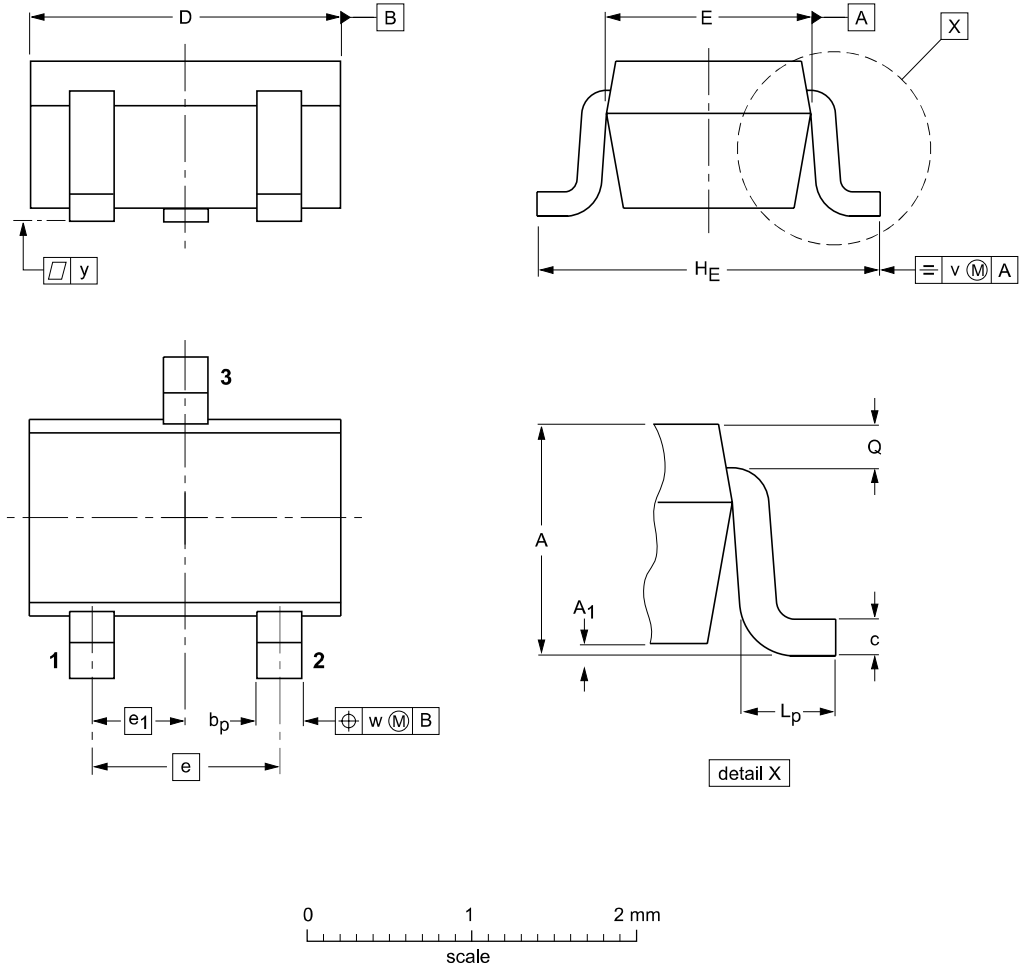
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0.1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C = 100mA	120		400	
	h _{FE(2)}	V _{CE} =1V, I _C = 800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B = 80mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =800mA, I _B = 80mA			1.2	V
Transition frequency	f _T	V _{CE} =10V, I _C = 50mA, f=30MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			15	pF

RANK	SS8050W
RANGE	200 - 350
MARKING	Y1



Package Outline

SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-323	Tape/Reel, 7" reel	3000	EIA-481-1